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May 2015

FDMS8820

N-Channel PowerTrench® MOSFET
30 V, 160 A, 2.0 mΩ

Features

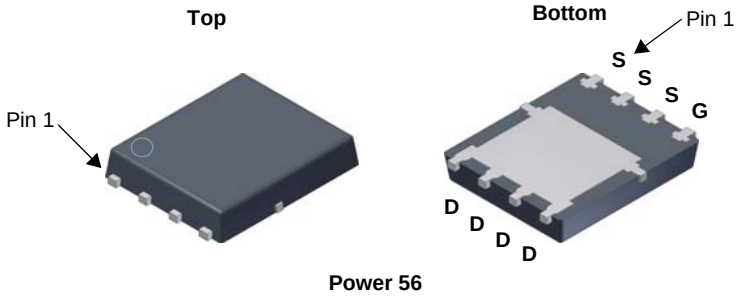
- Max $r_{DS(on)}$ = 2.0 mΩ at V_{GS} = 10 V, I_D = 28 A
- Max $r_{DS(on)}$ = 2.4 mΩ at V_{GS} = 4.5 V, I_D = 25 A
- Advanced Package and Silicon combination for low $r_{DS(on)}$ and high efficiency
- Next generation enhanced body diode technology, engineered for soft recovery
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

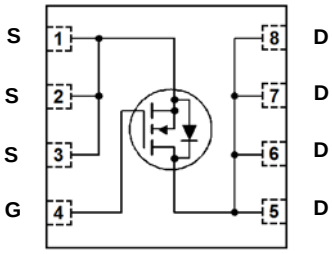
General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency and to minimize switch node ringing of DC/DC converters using either synchronous or conventional switching PWM controllers.It has been optimized for low gate charge, low $r_{DS(on)}$, fast switching speed and body diode reverse recovery performance.

Applications

- VRM Vcore Switching For Desktop And Server
- OringFET / Load Switching
- DC-DC Conversion





MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted.

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			30	V
V_{GS}	Gate to Source Voltage		(Note 4)	±20	V
I_D	Drain Current -Continuous	T_C = 25 °C	(Note 6)	160	A
	-Continuous	T_C = 100 °C	(Note 6)	101	
	-Continuous	T_A = 25 °C	(Note 1a)	28	
	-Pulsed		(Note 5)	634	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	294	mJ
P_D	Power Dissipation	T_C = 25 °C		78	W
	Power Dissipation	T_A = 25 °C	(Note 1a)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.6	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS8820	FDMS8820	Power 56	13 ”	12 mm	3000 units

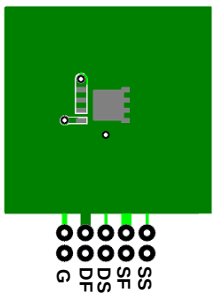
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Electrical Characteristics T_J = 25 °C unless otherwise noted.

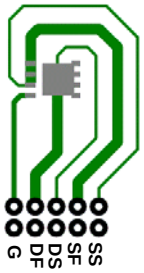
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		19		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current, Forward	V_{GS} = 20 V, V_{DS} = 0 V			100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	1.2	1.5	2.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-6		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 28 A		1.4	2.0	mΩ
		V_{GS} = 4.5 V, I_D = 25 A		1.8	2.4	
		V_{GS} = 10 V, I_D = 28 A, T_J = 125 °C		2.0	2.8	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 28 A		76		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		3995	5315	pF
C_{oss}	Output Capacitance			1295	1725	pF
C_{rss}	Reverse Transfer Capacitance			177	270	pF
R_g	Gate Resistance		0.1	1.1	2.5	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 15 V, I_D = 28 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		14	25	ns
t_r	Rise Time			7.7	16	ns
$t_{d(off)}$	Turn-Off Delay Time			41	66	ns
t_f	Fall Time			6.4	13	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 15 V, I_D = 28 A		63	88	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 4.5 V; V_{DD} = 15 V, I_D = 28 A		30	42	nC
Q_{gs}	Gate to Source Charge	V_{DD} = 15 V, I_D = 28 A		9.8		nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = 15 V, I_D = 28 A		8.2		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 2.0 A (Note 2)		0.7	1.1	V
		V_{GS} = 0 V, I_S = 28 A (Note 2)		0.8	1.2	
t_{rr}	Reverse Recovery Time	I_F = 28 A, di/dt = 100 A/μs		43	69	ns
Q_{rr}	Reverse Recovery Charge			27	43	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta CA}$ is determined by the user's board design.



a. 50 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b. 125 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. E_{AS} of 294 mJ is based on starting T_J = 25 °C; N-ch: L = 3 mH, I_{AS} = 14 A, V_{DD} = 30 V, V_{GS} = 10 V. 100% test at L = 0.1 mH, I_{AS} = 45 A.
4. As an N-ch device, the negative Vgs rating is for low duty cycle pulse occurrence only. No continuous rating is implied.
5. Pulsed Id please refer to SOA curve for more details.
6. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

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Typical Characteristics T_J = 25 °C unless otherwise noted.

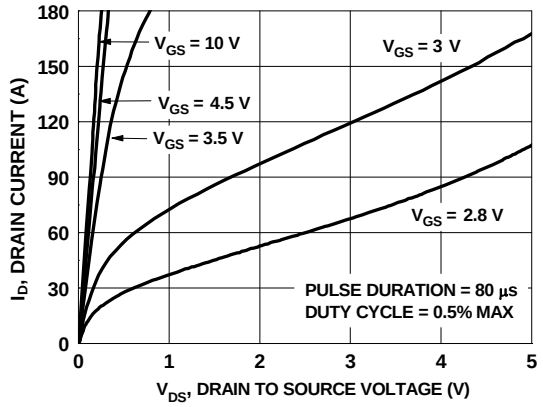


Figure 1. On Region Characteristics

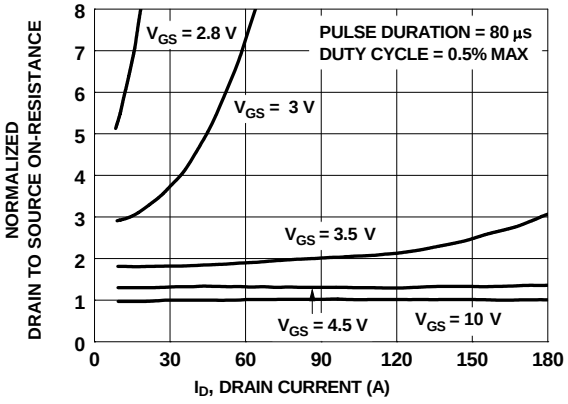


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

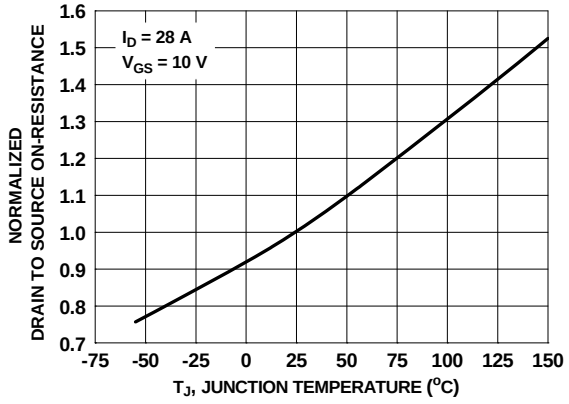


Figure 3. Normalized On Resistance vs. Junction Temperature

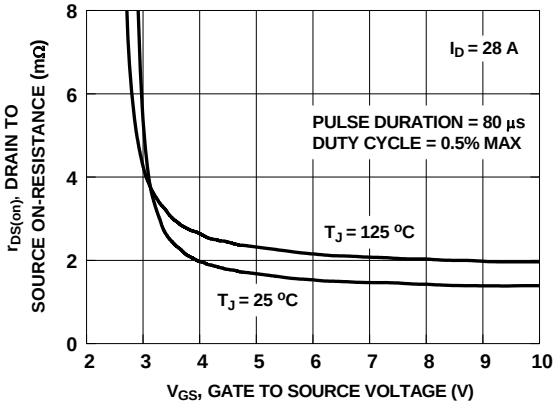


Figure 4. On-Resistance vs. Gate to Source Voltage

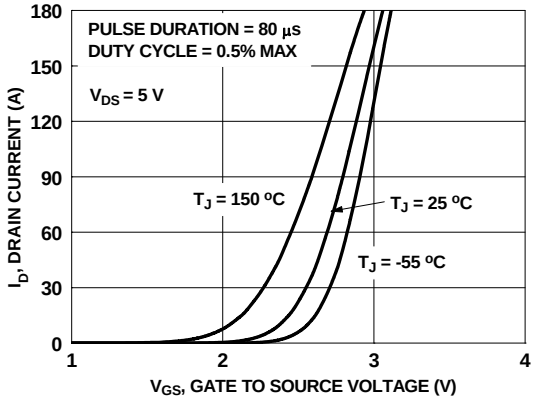


Figure 5. Transfer Characteristics

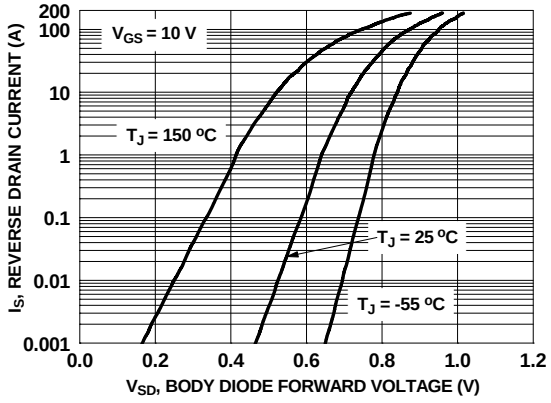


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

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Typical Characteristics T_J = 25 °C unless otherwise noted.

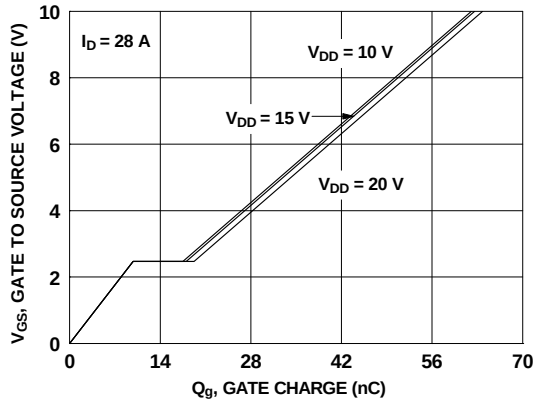


Figure 7. Gate Charge Characteristics

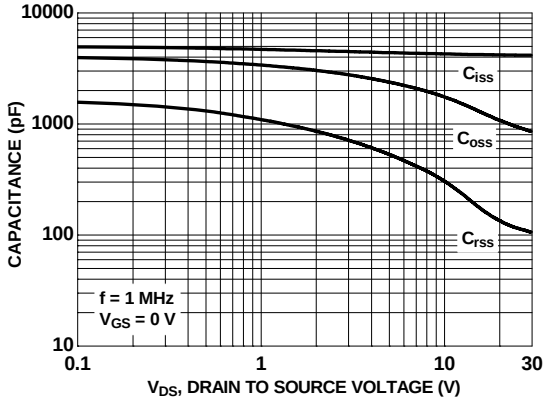


Figure 8. Capacitance vs. Drain to Source Voltage

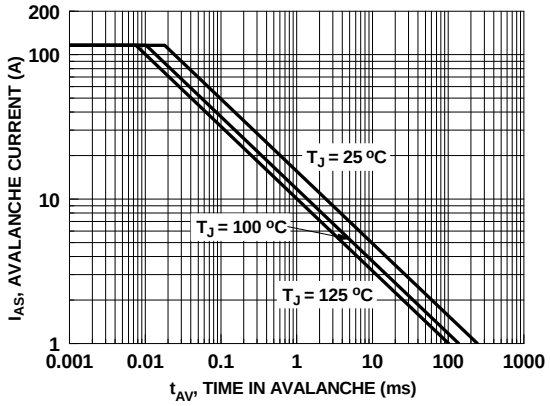


Figure 9. Unclamped Inductive Switching Capability

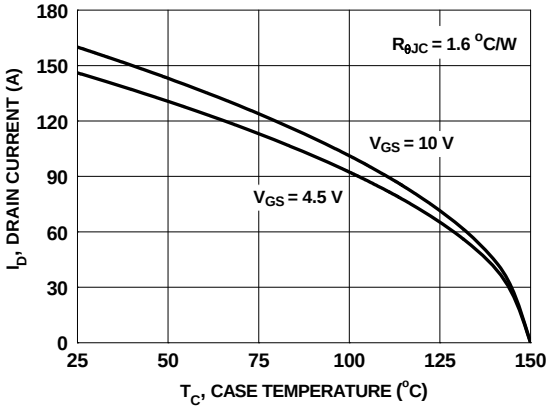


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

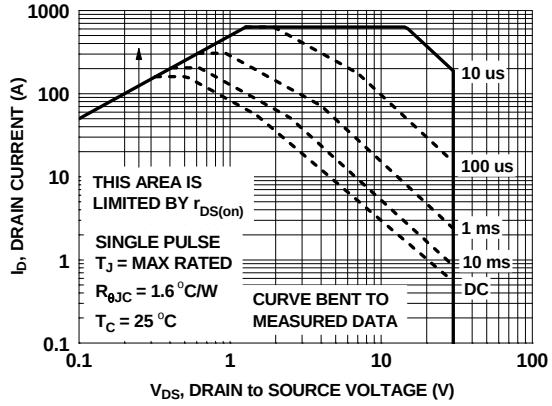


Figure 11. Forward Bias Safe Operating Area

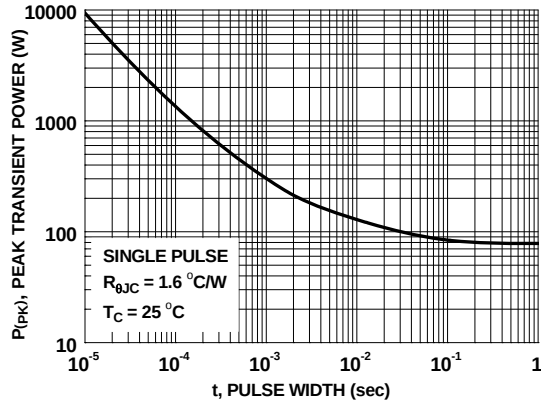


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted.

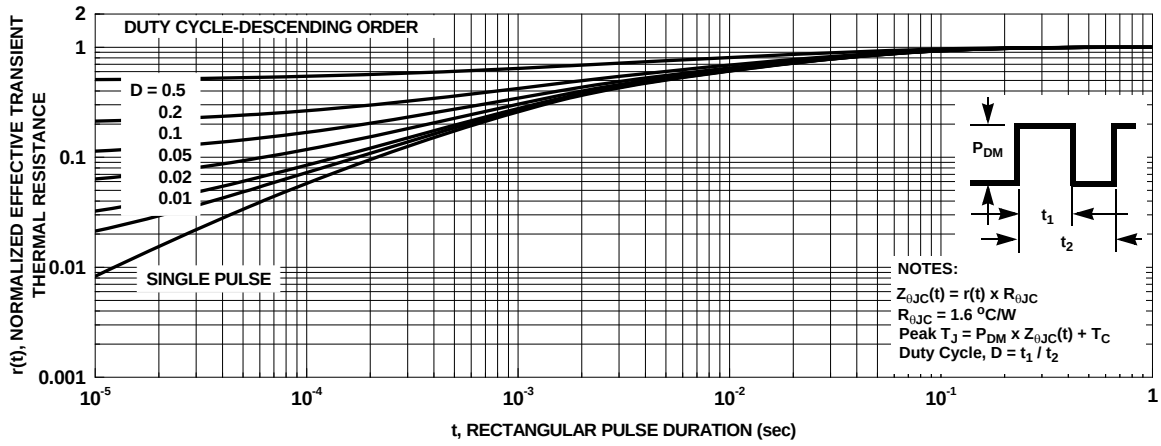
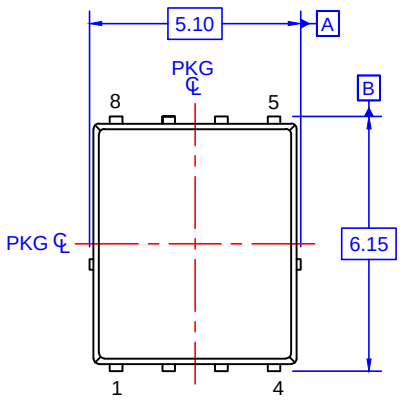
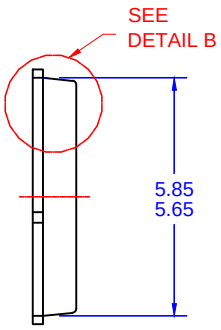


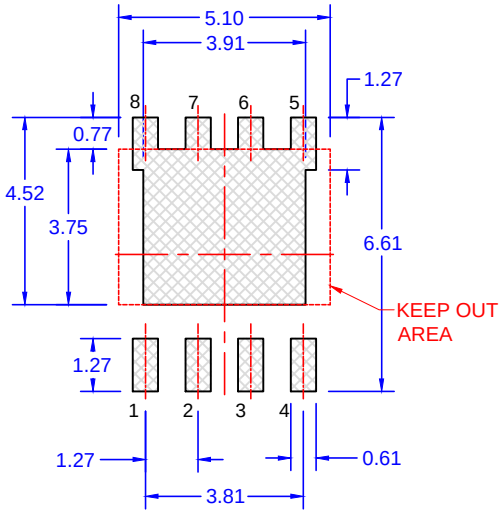
Figure 13. Junction-to-Case Transient Thermal Response Curve

PQFN8 5X6, 1.27P
CASE 483AE
ISSUE A

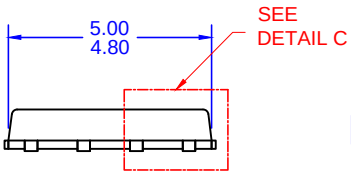


TOP VIEW

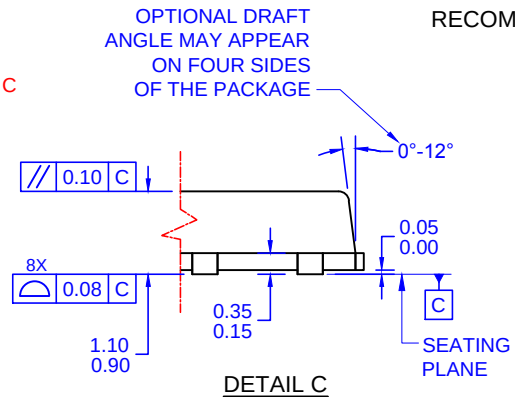




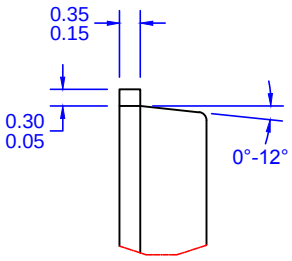
LAND PATTERN
RECOMMENDATION



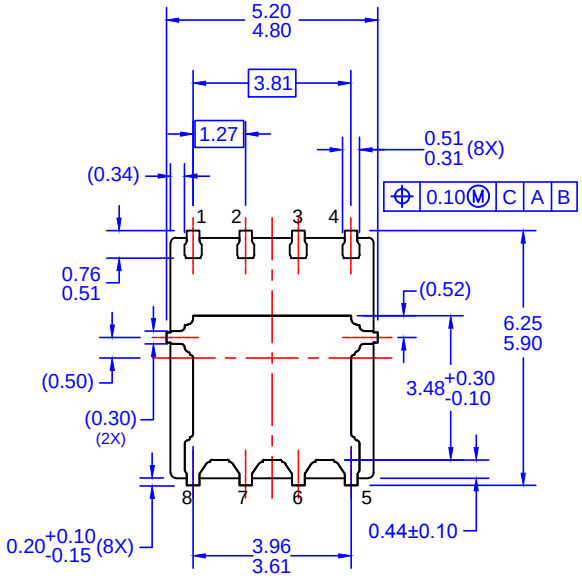
SIDE VIEW



DETAIL C
SCALE: 2:1



DETAIL B
SCALE: 2:1



BOTTOM VIEW

NOTES: UNLESS OTHERWISE SPECIFIED

A. PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA,.
B. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
C. ALL DIMENSIONS ARE IN MILLIMETERS.
D. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
E. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.

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